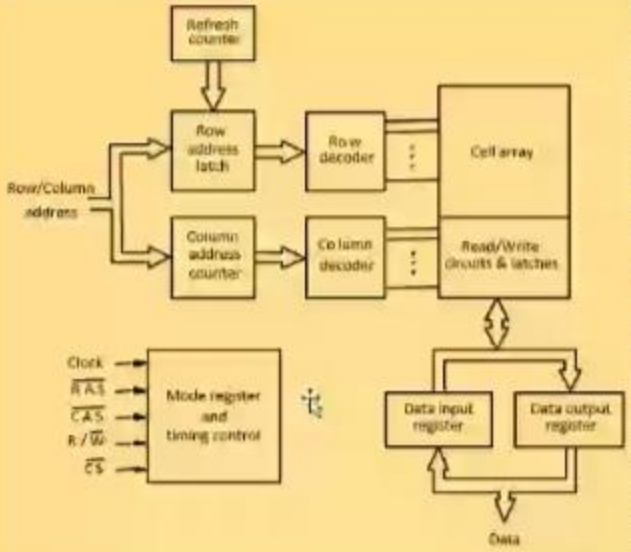
Click to add title

	0	1			M-1
0			.....		
1			.		
2			.		
			.		
			.		
N-1					

Fast Page Mode

- Suppose if we want to access the consecutive bytes in the selected row.
- This can be done without having to reselect the row.
  - Add a latch at the output of the sense circuits in each row.
  - All the latches are loaded when the row is selected.
  - Different column addresses can be applied to select and place different bytes on the data lines.
- Consecutive sequence of column addresses can be applied under the control signal CAS, without reselecting the row.
  - Allows a block of data to be transferred at a much faster rate than random accesses.
  - A small collection/group of bytes is usually referred to as a block.
- This transfer capability is referred to as the fast page mode feature.

Synchronous DRAMs



- *Operation is directly synchronized with processor clock signal.*
- *The outputs of the sense circuits are connected to a latch.*
- *During a Read operation, the contents of the cells in a row are loaded onto the latches.*
- *During a refresh operation, the contents of the cells are refreshed without changing the contents of the latches.*
- *Data held in the latches correspond to the selected columns are transferred to the output.*
- *For a burst mode of operation, successive columns are selected using column address counter and clock. CAS signal need not be generated externally. A new data is placed during raising edge of the clock*

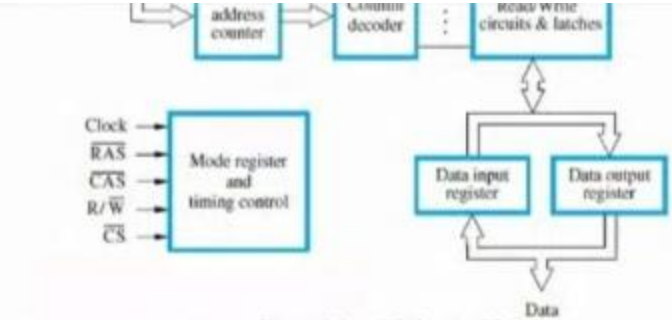


Figure 8.8 Synchronous DRAM.

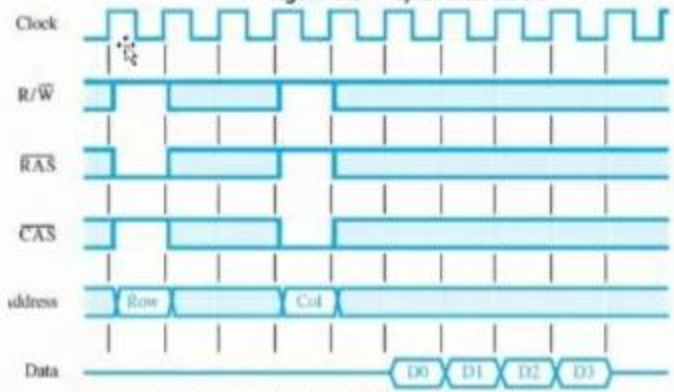


Figure 8.9 A burst read of length 4 in an SDRAM.

- First, the row-address is latched under control of RAS' signal (Figure 8.9).
- The memory typically takes 2 or 3 clock cycles to activate the selected row.
- Then, the column-address is latched under the control of CAS' signal.
- After a delay of one clock cycle, the first set of data bits is placed on the data-lines.
- SDRAM automatically increments column-address to access next 3 sets of bits in the selected row.